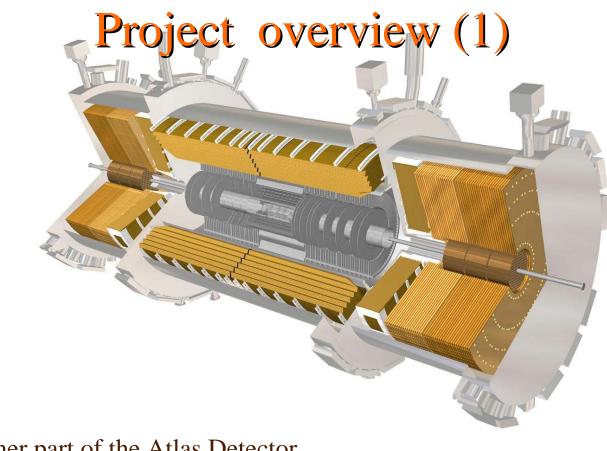
Radiation tests for ATLAS cold electronic

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Things to talk about

- Project overview
- Process selection strategy
- Measurement setup one transistor
- Radiation test setup in Rez
- Status & conclusions & plans



Inner part of the Atlas Detector at CERN (Geneva) with the HEC (Hadronic End Cap)

•This part is cooled with liquid argon.

•The amplifiers for signal read out are placed at the outer side of the HEC wheel.

•The beam (proton proton collision) travels along the middle axis.

Project overview (2)



Photo of a small part of the HEC wheel:

- •The Copper plates are the signal detector.
- •The Amplifier boards are connected with coaxial cables.
- •Several amplifier systems are assembled on one board.
- •If the detector runs, the amplifiers have to operate for 10 years under radiation, without loosing their characteristics.

Technology selection – strategy

Goals: * Radiation hardness should improve by a factor 10

* System should work both at room temperature & in liquid argon (-190°C)

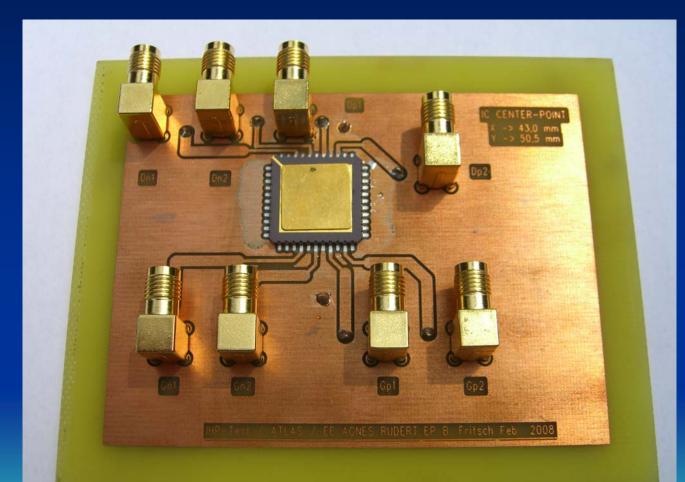
Radiation Hardness for 10years SLHC

50kGy 1.5*10¹⁵ cm⁻² 1.2*10¹² cm⁻² Gamma Ray Neutrons Protons

safety factor 20 (at the moment we measure Neutrons.)

Select a technology according to the following criteria:
⇒Prove the transistors are radiation hard
⇒Understand the temperature dependence
⇒ Study the Noise behaviour
⇒ Clarify the development surrounding with the company/ collaborator

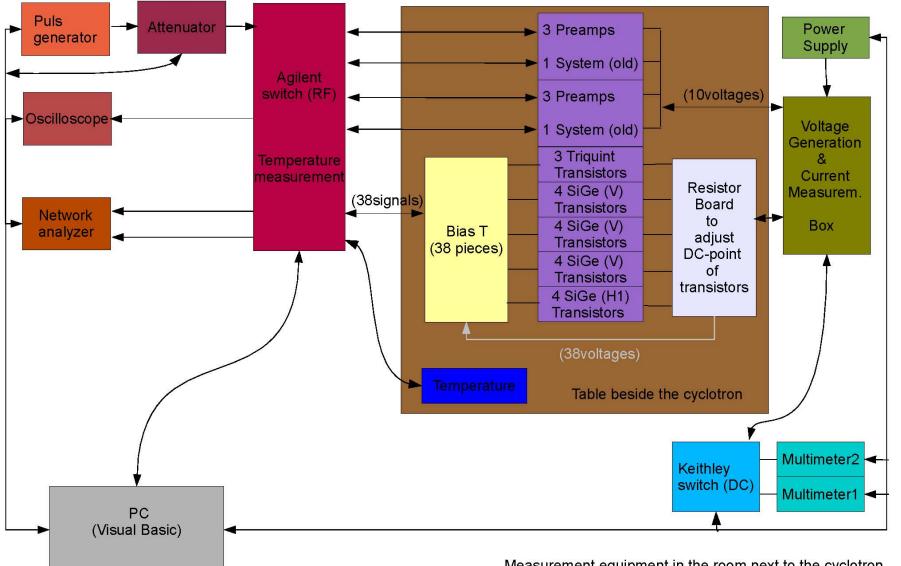
Measurement setup single transistors



Testboard for transistors:

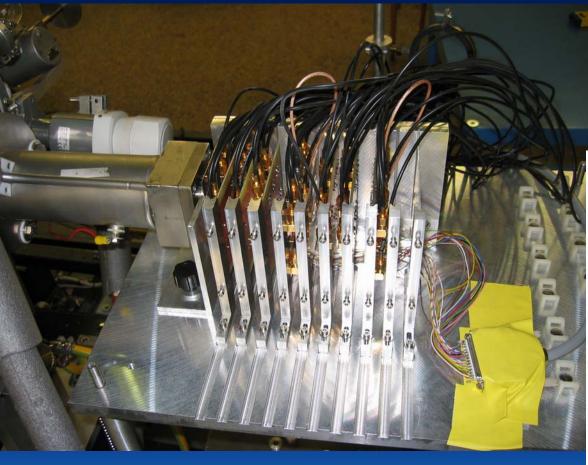
Four structures (2n, 2p) are bonded in this ceramic package.

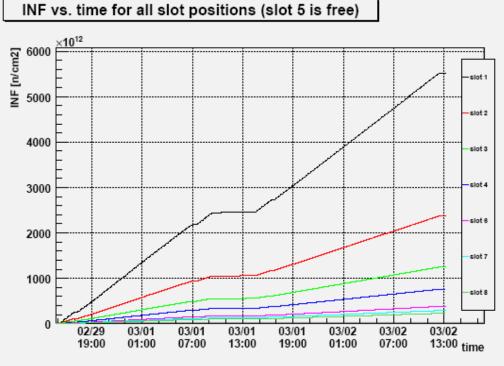
Radiation tests Setup in Rez (1)



Measurement equipment in the room next to the cyclotron

Radiation tests Setup in Rez (2)





Status & Conclusions & Plans

- •MOS & Bipolar transistors seem to be quite radiation hard in the range of test.
- Cold tests with liquid nitrogen show the temperature dependence of Bipolar Transistors. (Advantage for MOS)
- At the moment we measure noise figures of different transistors.
- •After that we make a process selection and start with the circuit design.

